L Number	Hits	Search Text	DB	Time stamp
1	7369	<pre>(((((silicon near on insulator) (SOI))) and ((silicon near oxide) (sio."sub.2"))) and (silicon near (substrate base pad wafer))) and (silicon near layer)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/05 16:23
2	1793	<pre>(((((((silicon near on insulator) (SOI))) and ((silicon near oxide) (sio."sub.2"))) and (silicon near (substrate base pad wafer))) and (silicon near layer)) and ((refractory near metal) (titanium near tungsten) (titanium near nitride))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 16:25

L Number	Hits	Search Text	DB	Time stamp
49	220768	((silicon near on insulator) (SOI))	USPAT;	2002/11/05 13:22
	-		US-PGPUB;	i
	,		EPO; JPO;	!
,			DERWENT;	!
			IBM_TDB	
50	25450	, , , , = = = = = = = = = = = = = = = , , , , = = = = = = = = = = , , , , =	USPAT;	2002/11/05 13:23
		((silicon near oxide) (sio."sub.2"))	US-PGPUB;	1
			EPO; JPO;	1
			DERWENT; IBM TDB	
51	12751	((((silicon near on insulator) (SOI))) and	USPAT;	2002/11/05 13:24
	12/51	((silicon near oxide) (sio."sub.2"))) and	US-PGPUB;	2002/11/03 13.24
ł		(silicon near (substrate base pad wafer))	EPO; JPO;	
!		(0222001 11042 (040001400 2400 pau 114201),	DERWENT;	
!			IBM TDB	'
53	7369	(((((silicon near on insulator) (SOI)))	USPĀT;	2002/11/05 13:32 '
		and ((silicon near oxide) (sio."sub.2")))	US-PGPUB;	
		and (silicon near (substrate base pad	EPO; JPO;	1
		wafer))) and (silicon near layer)	DERWENT;	1
			IBM_TDB	
54	904	((((()))	USPAT;	2002/11/05 13:33
	ı	and ((silicon near oxide) (sio."sub.2")))	US-PGPUB;	
1		and (silicon near (substrate base pad	EPO; JPO;	
		wafer))) and (silicon near layer)) and	DERWENT; IBM TDB	
!		(refractory near metal)	TOM IND	